



SUPER WIDEBAND, HIGH GAIN

Monolithic Amplifier Die **PMA3-453-D+**

50Ω 10 to 45 GHz

THE BIG DEAL

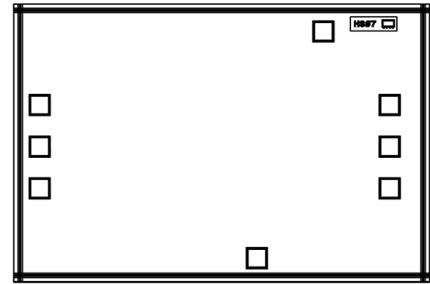
- Wideband, 10 to 45 GHz
- Usable down to 9 GHz
- High Gain, 25.5 dB typ. at 20 GHz
- Low NF, 1.6 dB typ. at 20 GHz
- P1dB, 10 dBm typ. at 20 GHz
- OIP3, 22 dBm typ. at 20 GHz
- Built-in Bias Tee and DC Blocks
- Patent Pending

APPLICATIONS

- 5G
- Lab Instrument
- Satellite

PRODUCT OVERVIEW

The PMA3-453-D+ is a PHEMT based wideband, low noise MMIC amplifier die with a unique combination of high gain and low noise figure over a very board bandwidth making it ideal for using as the first stage driver amplifier of receiver applications. This design operates on a single 4V supply, and is matched to 50 Ohm.



+RoHS Compliant
 The +Suffix identifies RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications

SEE ORDERING INFORMATION ON THE LAST PAGE

KEY FEATURES

Feature	Advantages
Low NF (<3.0dB typ.) up to 30GHz	Enables lower system noise figure performance.
High Gain 20dB typ. up to 30GHz	Enables signal amplification without the need for multiple gain stage, minimizing the effect of subsequent stages on noise figure.
Built-in Bias Tee & DC Blocks	Minimizes the external component count & PC board space, making it less expensive and user friendly for system designers.
Unpackaged Die	Enables users to integrate it directly into hybrids.

REV. A
 ECO-011060
 PMA3-453-D+
 MCLNY
 211213





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ELECTRICAL SPECIFICATIONS¹ AT 25°C, 50Ω, UNLESS NOTED

Parameter	Condition (GHz)	Vs=4.0V			Units
		Min.	Typ.	Max.	
Frequency Range	—	10		45	GHz
Noise Figure	10		1.9		dB
	20		1.6		
	30		2.4		
	40		3.8		
	45		5.2		
Gain	10		25.3		dB
	20		25.5		
	30		18.2		
	40		14.1		
	45		9.1		
Input Return Loss	10		13		dB
	20		21		
	30		8		
	40		5		
	45		5		
Output Return Loss	10		12		dB
	20		10		
	30		9		
	40		15		
	45		7		
Output Power @ 1 dB compression	10		8.5		dBm
	20		10.0		
	30		11.0		
	40		11.7		
	45		10.1		
Output IP3	10		18.6		dBm
	20		22.0		
	30		23.4		
	40		21.9		
	45		21.4		
Supply Voltage (Vs)		3.75	4.0	4.25	V
Device Operating Current (IDD)			68	112	mA
Device Current Variation vs. Temperature ²			-50		μA/°C
Device Current Variation vs. Voltage			0.02		mA/mV
Thermal Resistance, junction-to-ground lead			106		°C/W

1. Die is packaged in 3x3mm 12L MCLP and soldered on Mini-Circuits Characterization test board TB-PMA3-453+ with thru-line loss being deducted. See Characterization Test Circuit (Fig. 1)
 2. Device Current Variation vs. Temperature = (Current at 85°C - Current at -45°C)/130°C

MAXIMUM RATINGS³

Parameter	Ratings
Operating temperature (ground lead)	-40°C to 85°C
Junction Temperature	146°C
Total Power Dissipation	0.65W
Input Power (CW), Vs=4V	+23 dBm (5 minutes max.) +13 dBm (continuous)
DC Voltage (RF-IN & RF-OUT)	2V
DC voltage (Vs)	6V

3. Permanent damage may occur if any of these limits are exceeded.
 Electrical maximum ratings are not intended for continuous normal operation.

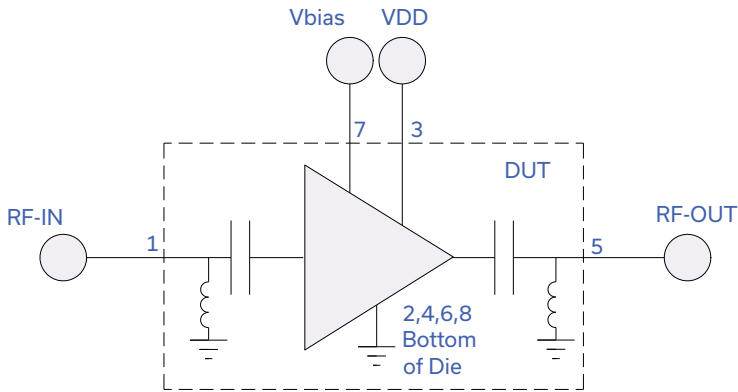




SUPER WIDEBAND, HIGH GAIN

Monolithic Amplifier Die **PMA3-453-D+**

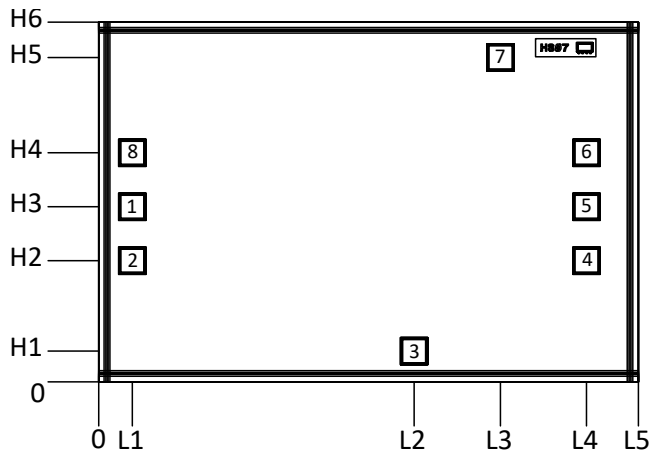
SIMPLIFIED SCHEMATIC



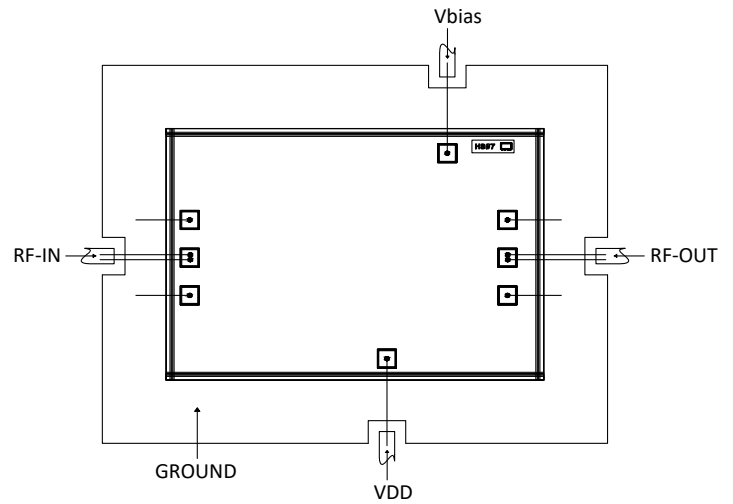
PAD DESCRIPTION

Function	Pad Number	Description
RF-IN	1	RF Input Pad. Connects to RF input
RF-OUT	5	RF Output Pad. Connects to RF output
VDD	3	DC Power Supply Pad. Connects to Voltage Source Vs via R1
VBias	7	Connects to VDD
Ground	2,4,6,8 & Bottom of Die	Connects to ground

BONDING PAD POSITION



ASSEMBLY DIAGRAM



DIMENSION IN μM , TYPICAL

L1	L2	L3	L4	L5	H1	H2	H3	H4	H5	H6	Thick-ness	Die Size	Pad Size 1,2,3,4,5, 6,7 & 8
93.0	877.0	1117.0	1356.0	1500.0	85.0	337.0	487.0	637.0	902.0	1000.0	100	1500 x 1000	64 x 64



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RECOMMENDED APPLICATION AND CHARACTERIZATION TEST CIRCUIT

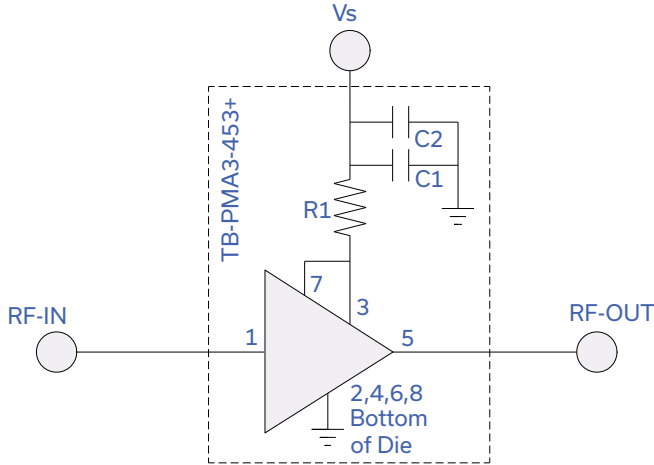


Fig 1. Application and Characterization Circuit

Note: This block diagram is used for characterization. (Die is packaged in 3x3mm 12L MCLP and soldered on Mini-Circuits Characterization Test Board TB-PMA3-453+) Gain, Return Loss, Output Power at 1dB Compression (P1dB), Output IP3(OIP3), and Noise Figure are measured using Agilent's N4245A microwave network analyzer.

Conditions:

1. Gain and Return loss: Pin= -25dBm
2. Output IP3 (OIP3): Two tones, spaced 1 MHz apart, -5dBm/tone at output.

Component	Size	Value	Part Number	Manufacturer
R1	0603	18 Ohm	SG73G1JTTD18R0C	Koa
C1	0402	5pF	GJM1555C1H5ROCB01D	Murata
C2	0402	0.1uF	GRM155R71C104KA88D	Murata

ASSEMBLY PROCEDURE

1. Storage
Dice should be stored in a dry nitrogen purged desiccators or equivalent.
2. ESD
MMIC PHEMT amplifier dice are susceptible to electrostatic and mechanical damage. Die are supplied in antistatic protected material, which should be open in clean room conditions at an appropriately grounded anti-static workstation.
3. Die Handling and Attachment
Devices need careful handling using correctly designed collets, it is recommended to handle the chip along the edges with a custom design collet. The die mounting surface must be clean and flat. Using conductive silver filled epoxy, recommended epoxies are Ablestik 84-1 LMISR4 or equivalents. Apply sufficient epoxy to meet required epoxy bond line thickness, epoxy fillet height and epoxy coverage around total periphery. Parts shall be cured in a nitrogen filled atmosphere per manufacturer's cure condition. The surface of the chip has exposed air bridges and should not be touched with vacuum collet, tweezers or fingers.
5. Wire Bonding
Bond pad openings in the surface passivation above the bond pads are provided to allow wire bonding to the dice gold bond pads. Thermo-sonic bonding is used with minimized ultrasonic content. Bond force, time, ultrasonic power and temperature are all critical parameters. Suggested wire is pure gold, 1mil diameter. Bonds must be made from the bond pads on the die to the packaged or substrate. All bond wires should be kept as short as low as reasonable to minimize performance degradation due to undesirable series inductance.





SUPER WIDEBAND, LOW NOISE

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ADDITIONAL DETAILED TECHNICAL INFORMATION IS AVAILABLE ON OUR DASH BOARD.

Performance Data	Data Table Swept Graphs S-Parameter (S2P Files) Data Set with and without port extension(.zip file)								
Case Style	Die								
Die Ordering and packaging information	<table border="0"> <tr> <td>Quantity, Package</td> <td>Model No.</td> </tr> <tr> <td>Small, Gel - Pak: 5,10,50,100 KGD*</td> <td>PMA3-453-DG+</td> </tr> <tr> <td>Medium†, Partial wafer: KGD*<1102</td> <td>PMA3-453-DP+</td> </tr> <tr> <td>Full Wafer</td> <td>PMA3-453-DF+</td> </tr> </table> <p>†Available upon request contact sales representative Refer to AN-60-067</p>	Quantity, Package	Model No.	Small, Gel - Pak: 5,10,50,100 KGD*	PMA3-453-DG+	Medium†, Partial wafer: KGD*<1102	PMA3-453-DP+	Full Wafer	PMA3-453-DF+
Quantity, Package	Model No.								
Small, Gel - Pak: 5,10,50,100 KGD*	PMA3-453-DG+								
Medium†, Partial wafer: KGD*<1102	PMA3-453-DP+								
Full Wafer	PMA3-453-DF+								
Environmental Ratings	ENV80								

*Known Good Die ("KGD") means that the dice in question have been subjected to Mini-Circuits DC test performance criteria and measurement instructions and that the parametric data of such dice fall within a predefined range. While DC testing is not definitive, it does provide a higher degree of confidence that die are capable of meeting typical RF electrical parameters specified by Mini-Circuits.

ESD RATING**

Human Body Model (HBM): Class 1A (250V) in accordance with ANSI/ESD STM 5.1 - 2001

**Tested in 3x3 12L MCLP package

NOTES

- A. Performance and quality attributes and conditions not expressly stated in this specification document are intended to be excluded and do not form a part of this specification document.
- B. Electrical specifications and performance data contained in this specification document are based on Mini-Circuit's applicable established test performance criteria and measurement instructions.
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